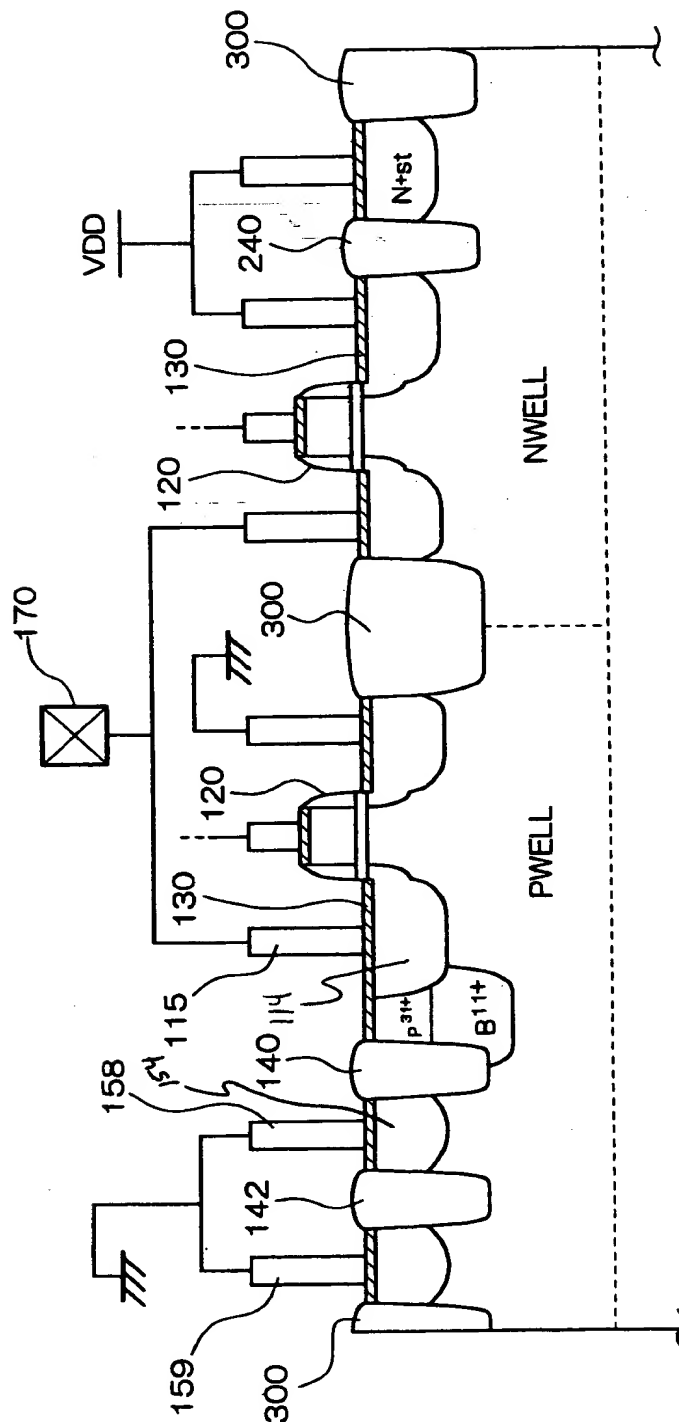
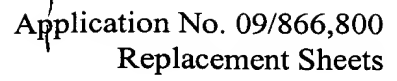


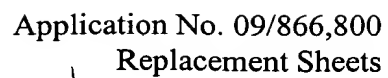
[illegible]

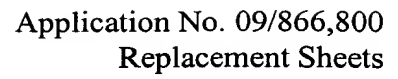


FIG. 22







[illegible]

This diagram shows a cross-sectional view of a semiconductor device. A substrate 200 is shown with a P+ region 212. A trench 216 is formed in the substrate, with a P+ region 214 at the bottom. A NWELL region 218 is formed in the substrate, with a P+ region 214 at the bottom. A gate stack 120 is formed on the substrate, with a gate dielectric 117 and a gate electrode 130. A source/drain region 240 is formed in the substrate, with a P+ region 214 at the bottom. A contact pad 222 is formed on the substrate, with a P+ region 214 at the bottom. A bonding pad 260 is formed on the contact pad. The device is labeled with various reference numerals: 100, 117, 120, 130, 200, 212, 214, 216, 218, 240, 260.